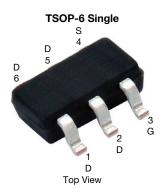


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Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	-60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.095			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.135			
I _D (A)	-5.3			
Configuration	Single			
Package	TSOP-6			

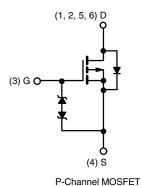
Marking Code: 8Y

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified c
- 100 % R_q and UIS tested
- Typical ESD protection 800 V
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE



ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3427AEEV (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	Drain-Source Voltage		-60	V	
Gate-Source Voltage		V_{GS}	± 20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Continuous Drain Current	T _C = 25 °C	- I _D	-5.3		
Continuous Drain Current	T _C = 125 °C		-3		
Continuous Source Current (Diode Conduction)		I _S	-6.3	A	
Pulsed Drain Current ^a		I _{DM}	-21	1	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	-21		
Single Pulse Avalanche Energy	L = 0.1 MH	E _{AS}	22	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	D	5	W	
	T _C = 125 °C	P_{D}	1.6	- vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount b	R_{thJA}	110	°C/W
Junction-to-Foot (Drain)		R_{thJF}	30	C/ VV

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. Parametric verification ongoing



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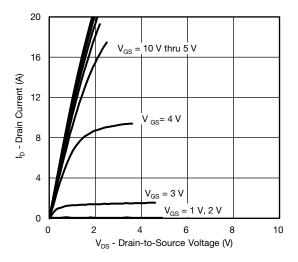
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$, $I_D = -250 \mu A$		-60	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-2	-2.5	V	
0.1. 0	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 10	A	
Gate-Source Leakage		V _{DS} =	0 V, V _{GS} = ± 10 V	-	-	± 2	mA	
		$V_{GS} = 0 V$	V _{DS} = -60 V	-	-	-1	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	μΑ	
		V _{GS} = 0 V	V _{DS} = -60 V, T _J = 175 °C	-	-	-150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 \text{ V}$	-10	-	-	Α	
		V _{GS} = -10 V	I _D = -4.5 A	-	0.079	0.095	Ω	
Drain-Source On-State Resistance a	В	V _{GS} = -10 V	I _D = -4.5 A, T _J = 125 °C	-	-	0.148		
Drain-Source On-State Resistance "	R _{DS(on)}	V _{GS} = -10 V	I _D = -4.5 A, T _J = 175 °C	-	-	0.178		
		V _{GS} = -4.5 V	I _D = -3.5 A	-	0.112	0.135		
Forward Transconductance ^a	9 _{fs}	V _{DS} = -15 V, I _D = -4 A		-	9	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	700	1000	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V, f} = 1 \text{ MHz}$	-	90	120		
Reverse Transfer Capacitance	C_{rss}			-	50	75		
Total Gate Charge ^c	Qg			-	15.3	22		
Gate-Source Charge ^c	Q_{gs}	$V_{GS} = -10 \text{ V}$	$V_{DS} = -30 \text{ V}, I_{D} = -5 \text{ A}$	-	2.5	-	nC	
Gate-Drain Charge c	Q_{gd}		1		5.4	-	1	
Gate Resistance	Rg	f = 1 MHz		2.7	5.4	8.1	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	8	12		
Rise Time ^c	t _r	V_{DD} = -30 V, R_L = 6 Ω $I_D \cong$ -5 A, V_{GEN} = -10 V, R_g = 1 Ω		-	24	35	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	26	38		
Fall Time ^c	t _f			-	33	50		
Source-Drain Diode Ratings and Chara	cteristics b	•						
Pulsed Current ^a	I _{SM}			-	-	-21	Α	
Forward Voltage	V_{SD}	I _F =	-	-0.8	-1.2	V		

Notes

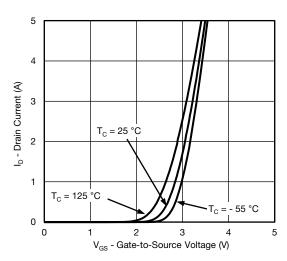
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

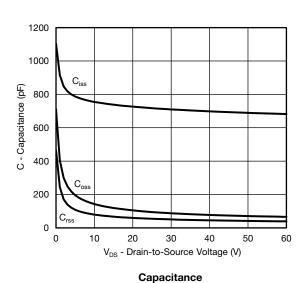


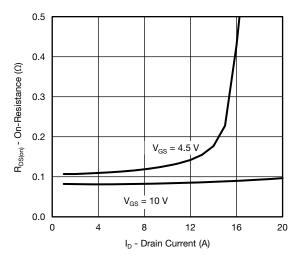


Output Characteristics

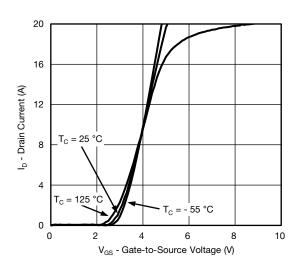


Transfer Characteristics

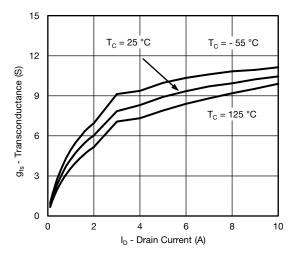




On-Resistance vs. Drain Current and Gate Voltage

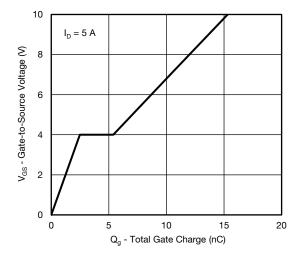


Transfer Characteristics

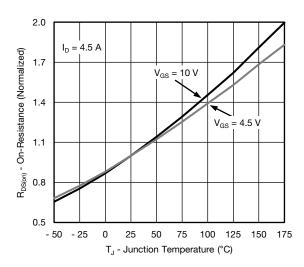


Transconductance

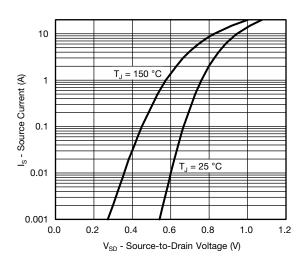




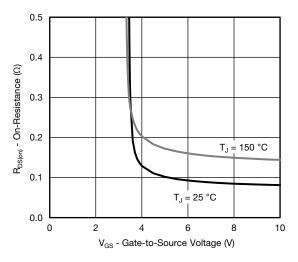
Gate Charge



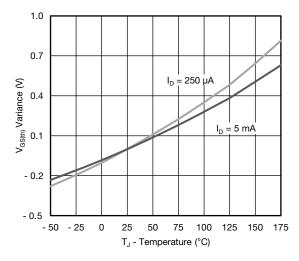
On-Resistance vs. Junction Temperature



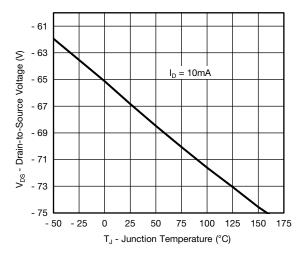
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

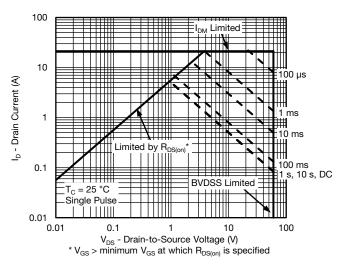


Threshold Voltage

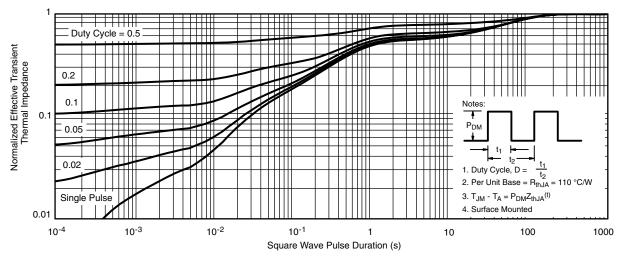


Drain-to-Source Voltage vs. Junction Temperature



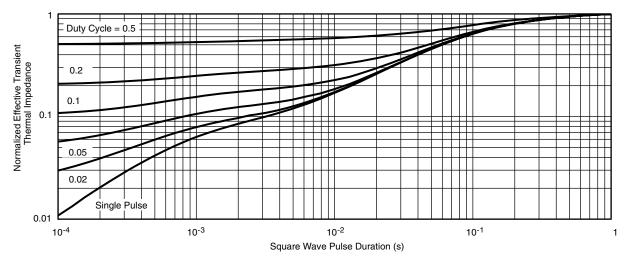


Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Foot

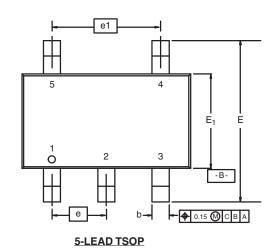
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65333.

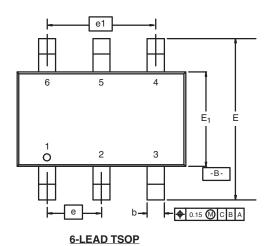


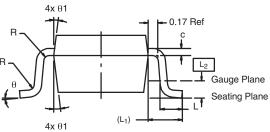


TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C







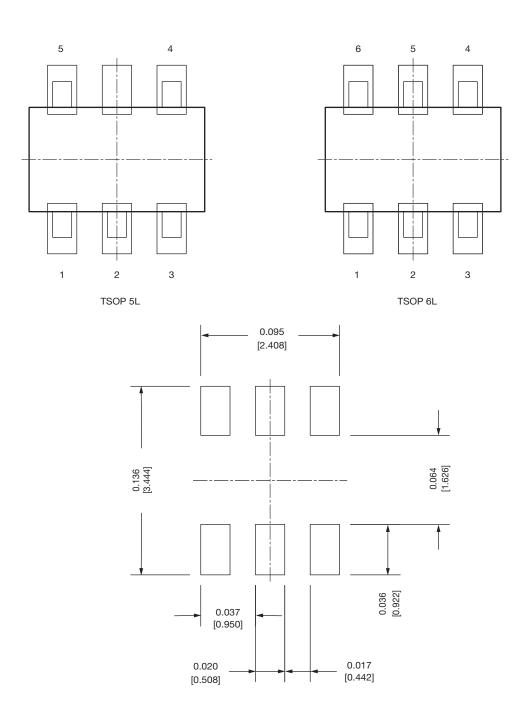
D —	-A-
0.08 C	A ₂ A A ₂ A Seating Plane

	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116 0.120		0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁		0.60 Ref		0.024 Ref			
L ₂		0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ1	7° Nom 7° Nom						
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Document Number: 71200 www.vishay.com 18-Dec-06



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010

Revision: 24-Oct-2022 1 Document Number: 72610





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